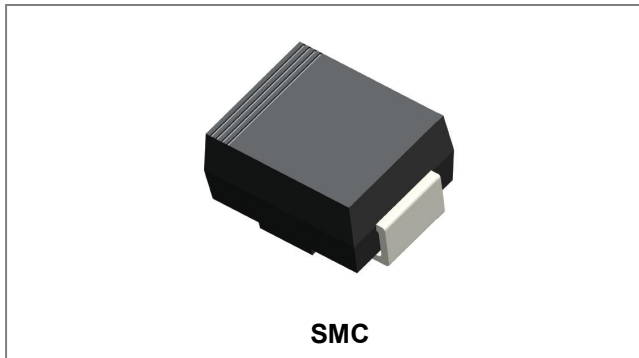


## 30BQ150 SCHOTTKY RECTIFIER



### Features

- Small foot print, surface mountable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb - Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Circuit Diagram



### Applications

- Disk Drives
- Switching power supply
- Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery Charging

### Maximum Ratings:

| Characteristics  | Symbol                          | Condition   | Max. | Units |
|--|---------------------------------|---|------|-------|
| Peak Repetitive Reverse Voltage<br>Working Peak Reverse Voltage<br>DC Blocking Voltage | $V_{RRM}$<br>$V_{RWM}$<br>$V_R$ | -   | 150  | V     |
| Average Rectified Forward Current  | $I_{F(AV)}$                     | 50% duty cycle @ $T_C=148^\circ\text{C}$ ,<br>rectangular wave form | 3.0  | A     |
| Peak One Cycle Non-Repetitive Surge Current  | $I_{FSM}$                       | 8.3 ms, half Sine pulse, $T_C=25^\circ\text{C}$                     | 55   | A     |

### Electrical Characteristics:

| Characteristics        | Symbol   | Condition   | Typ.    | Max.   | Units            |
|------------------------|----------|---|---------|--------|------------------|
| Forward Voltage Drop*  | $V_{F1}$ | @ 3 A, Pulse, $T_J = 25^\circ\text{C}$                                    | 0.79    | 0.86   | V                |
|                        | $V_{F2}$ | @ 3 A, Pulse, $T_J = 125^\circ\text{C}$                                   | 0.61    | 0.70   | V                |
| Reverse Current*       | $I_{R1}$ | @ $V_R = \text{Rated } V_R$ , Pulse, $T_J = 25^\circ\text{C}$             | 0.00004 | 1      | mA               |
|                        | $I_{R2}$ | @ $V_R = \text{Rated } V_R$ , Pulse, $T_J = 125^\circ\text{C}$            | 0.03    | 3      | mA               |
| Junction Capacitance   | $C_T$    | @ $V_R = 5\text{V}$ , $T_C = 25^\circ\text{C}$<br>$f_{SIG} = 1\text{MHz}$ | 80      | 110    | pF               |
| Series Inductance      | $L_S$    | Measured lead to lead 5 mm from<br>package body                           | 3.0     | -      | nH               |
| Voltage Rate of Change | dv/dt    | -   | -       | 10,000 | V/ $\mu\text{s}$ |

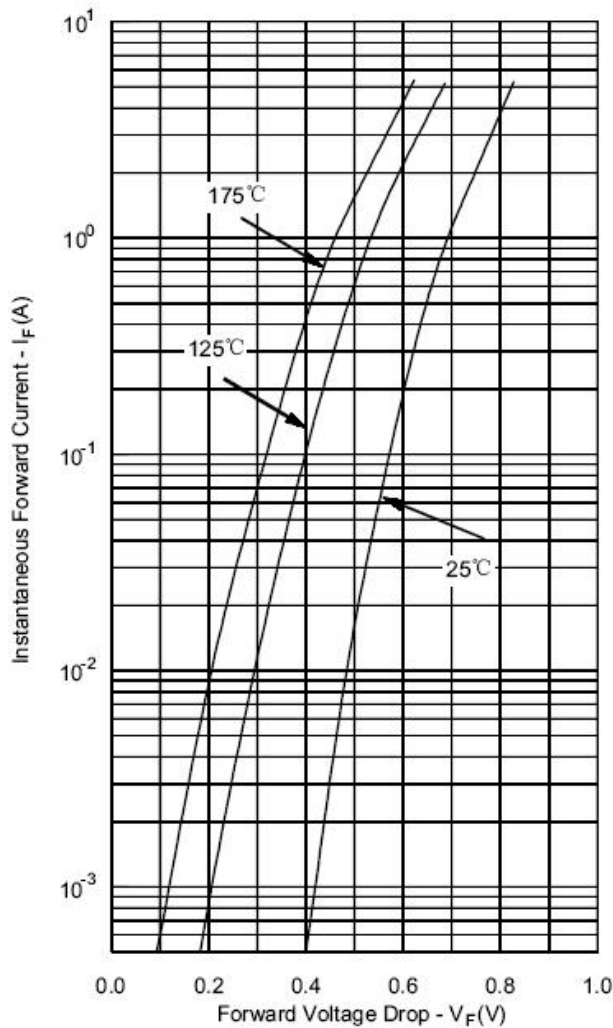
\* Pulse width < 300  $\mu\text{s}$ , duty cycle < 2%

**Thermal-Mechanical Specifications:**

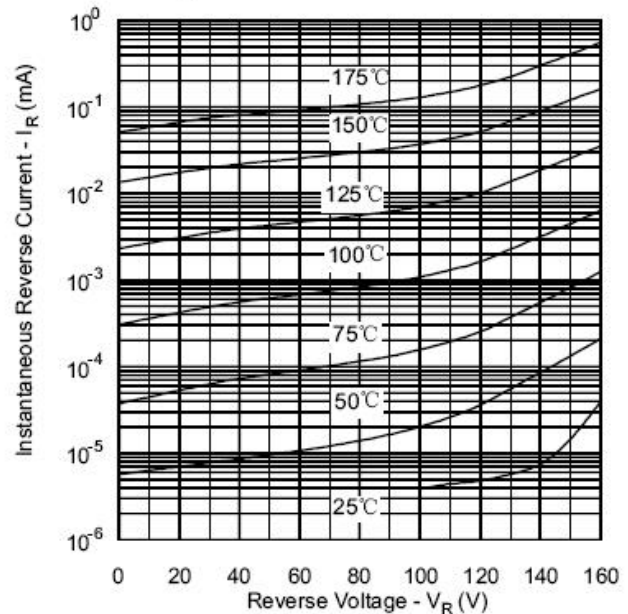
| Characteristics                             | Symbol          | Condition    | Specification | Units |
|---|-----------------|--------------|---------------|-------|
| Junction Temperature                        | $T_J$           | -            | -55 to +175   | °C    |
| Storage Temperature                         | $T_{stg}$       | -            | -55 to +175   | °C    |
| Typical Thermal Resistance Junction to Lead | $R_{\theta JL}$ | -            | 12            | °C/W  |
| Typical Thermal Resistance Junction to Case | $R_{\theta JA}$ | DC operation | 46            | °C/W  |
| Approximate Weight                          | wt              | -            | 0.21          | g     |
| Case Style                                  | SMC             |              |               |       |

**Ratings and Characteristics Curves**

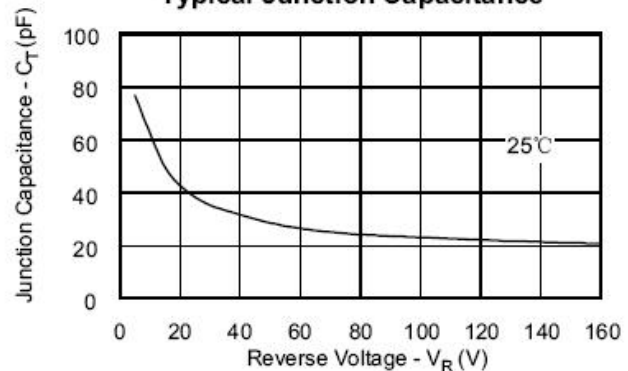
**Typical Forward Characteristics**



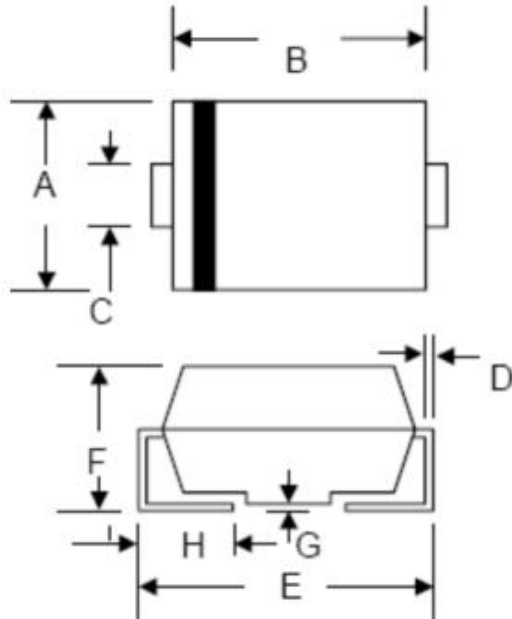
**Typical Reverse Characteristics**



**Typical Junction Capacitance**



**Mechanical Dimensions SMC**



| SYMBOL | Millimeters |       | Inches |       |
|--------|-------------|-------|--------|-------|
|        | Min.        | Max.  | Min.   | Max.  |
| A      | 5.59        | 6.22  | 0.220  | 0.245 |
| B      | 6.60        | 7.11  | 0.260  | 0.280 |
| C      | 2.75        | 3.25  | 0.108  | 0.128 |
| D      | 0.152       | 0.305 | 0.006  | 0.012 |
| E      | 7.75        | 8.25  | 0.305  | 0.325 |
| F      | 2.00        | 2.95  | 0.079  | 0.116 |
| G      | 0.051       | 0.203 | 0.002  | 0.008 |
| H      | 0.76        | 1.60  | 0.030  | 0.063 |


**Ordering Information**

| Device  | Package       | Shipping       |
|---------|---------------|----------------|
| 30BQ150 | SMC (Pb-Free) | 3000pcs / reel |

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

**Marking Diagram**

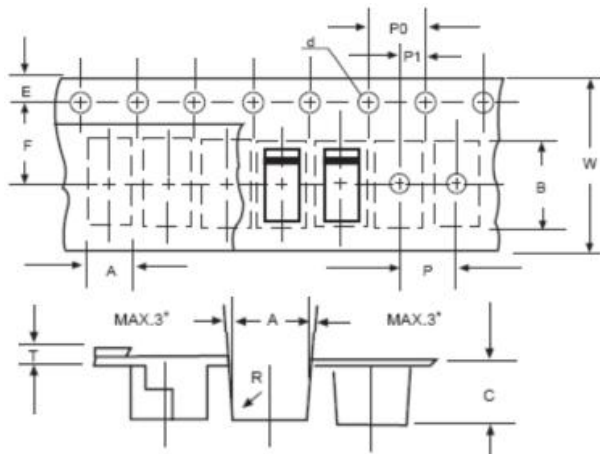
Where XXXXX is YYWWL



SC3M = Part Name  
YY = Year  
WW = Week  
L = Lot Number

**Cautions:** Molding resin  
Eooxv resin UL:94V-0

**Carrier Tape Specification SMC**



| SYMBOL | Millimeters |       |
|--------|-------------|-------|
|        | Min.        | Max.  |
| A      | 5.90        | 6.10  |
| B      | 8.20        | 8.40  |
| C      | 2.40        | 2.60  |
| d      | 1.40        | 1.60  |
| E      | 1.40        | 1.60  |
| F      | 7.60        | 7.70  |
| P      | 7.90        | 8.10  |
| P0     | 3.90        | 4.10  |
| P1     | 3.90        | 4.10  |
| T      | -           | 0.600 |
| W      | 15.80       | 16.20 |

**Technical Data**  
**Data Sheet N0677, Rev. A**



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